

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT89 (SC-62/TO-243) flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: 2PB1424.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	A
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 2 \text{ A}; I_{B} = 0.1 \text{ A}$	<u>[1]</u> _	0.2	0.5	V

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	emitter	_	
2	collector		2 J
3	base		3

3. Ordering information

Table 3. Orde	ering information	ation	
Type number	Package		
	Name	Description	Version
2PD2150	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4. Marking codes	
Type number	Marking code
2PD2150	M2

5. Limiting values

Table 5. Limiting values

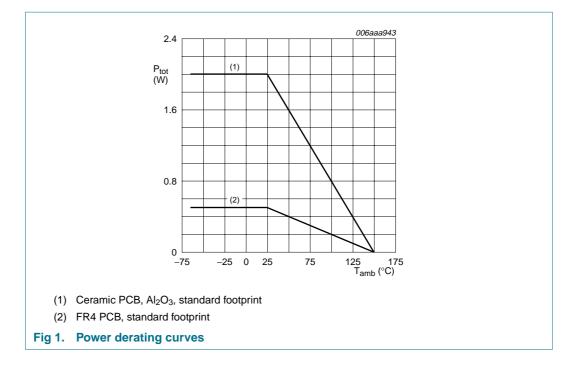
In accordance with the Absolute Maximum Rating System (IEC 60134).

		0) (/		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	40	V
V _{CEO}	collector-emitter voltage	open base	-	20	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	3	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	5	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	0.5	W
			[2] _	2	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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6. Thermal characteristics

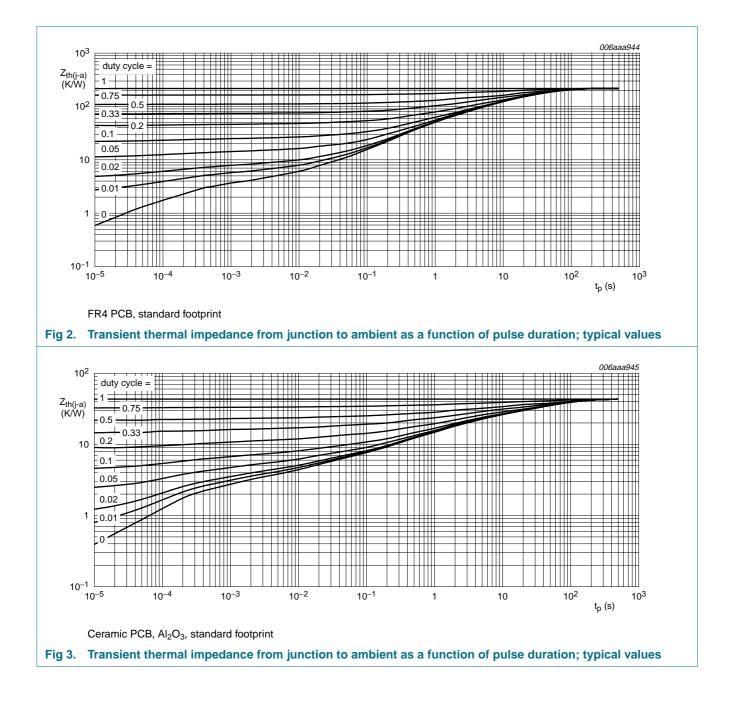
Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	250	K/W
			[2] _	-	62	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

2PD2150

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2PD2150

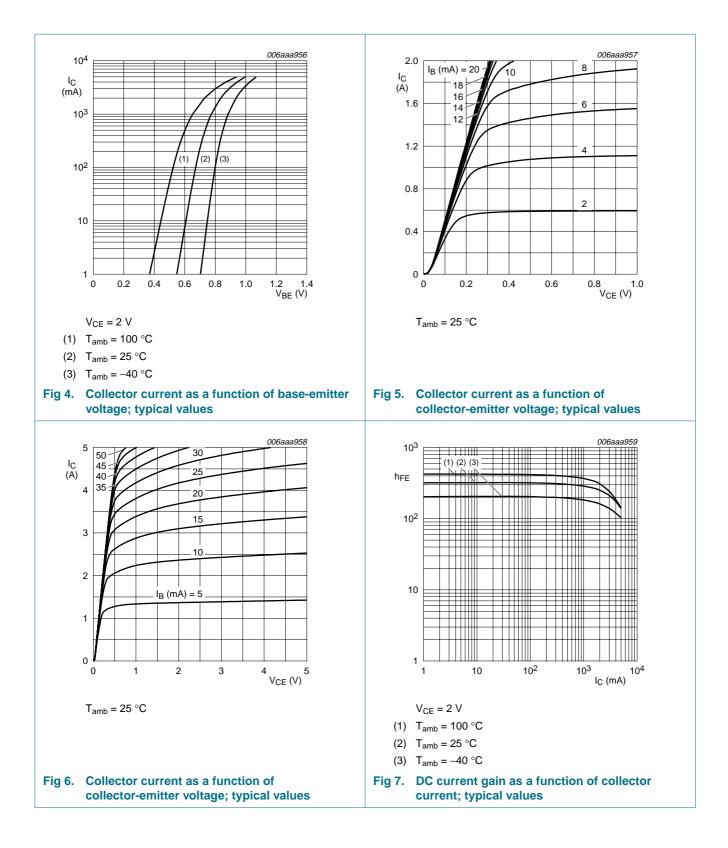
7. Characteristics

I_{CBO} collector-base cut-off current $V_{CB} = 30$ V; $I_E = 0$ A 0.7 I_{EBO} emitter-base cut-off current $V_{EB} = 5$ V; $I_C = 0$ A 0.7 h_{FE} DC current gain $V_{CE} = 2$ V; $I_C = 0.1$ A180 180-39	Table 7. $T_{amb} = 25$	Characteristics °C unless otherwise spec	cified.					
Constant of the first of the	Symbol	Parameter	Conditions		Min	Тур	Max	Unit
LBOCurrentVCBCURRENTCURRENTCURRENThFEDC current gain $V_{CE} = 2 \text{ V}; \text{ I}_{C} = 0.1 \text{ A}$ 180-39 V_{CEsat} collector-emitter saturation voltage $I_{C} = 2 \text{ A}; \text{ I}_{B} = 0.1 \text{ A}$ 11-0.20.5 f_{T} transition frequency f = 100 MHz $V_{CE} = 2 \text{ V}; \text{ I}_{E} = -0.5 \text{ A};$ f = 100 MHz-220- C_{ib} common-base input 	I _{CBO}		$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$		-	-	0.1	μΑ
$ \begin{array}{lllllllllllllllllllllllllllllll$	I _{EBO}		$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	0.1	μΑ
saturation voltage f_T transition frequency $V_{CE} = 2 \text{ V}; \text{ I}_E = -0.5 \text{ A};$ f = 100 MHz-220 - C_{ib} common-base input capacitance $V_{EB} = 5 \text{ V}; \text{ I}_E = i_e = 0 \text{ A};$ f = 1 MHz-180 - C_{ob} common-base output $V_{CB} = 10 \text{ V}; \text{ I}_E = i_e = 0 \text{ A};$ -20 -	h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 0.1 \text{ A}$		180	-	390	
$f = 100 \text{ MHz}$ $C_{ib} \qquad \text{common-base input} \qquad V_{EB} = 5 \text{ V}; I_E = i_e = 0 \text{ A}; \qquad - \qquad 180 - \\ f = 1 \text{ MHz} \qquad \qquad C_{ob} \qquad \text{common-base output} \qquad V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A}; \qquad - \qquad 20 - \qquad -$	V _{CEsat}		$I_{C} = 2 \text{ A}; I_{B} = 0.1 \text{ A}$	<u>[1]</u>	-	0.2	0.5	V
$\label{eq:capacitance} capacitance f = 1 \mbox{ MHz}$ $C_{ob} \mbox{ common-base output } V_{CB} = 10 \mbox{ V; } I_E = i_e = 0 \mbox{ A; } - 20 \mbox{ -}$	f _T	transition frequency			-	220	-	MHz
	C _{ib}				-	180	-	pF
	C _{ob}				-	20	-	pF

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

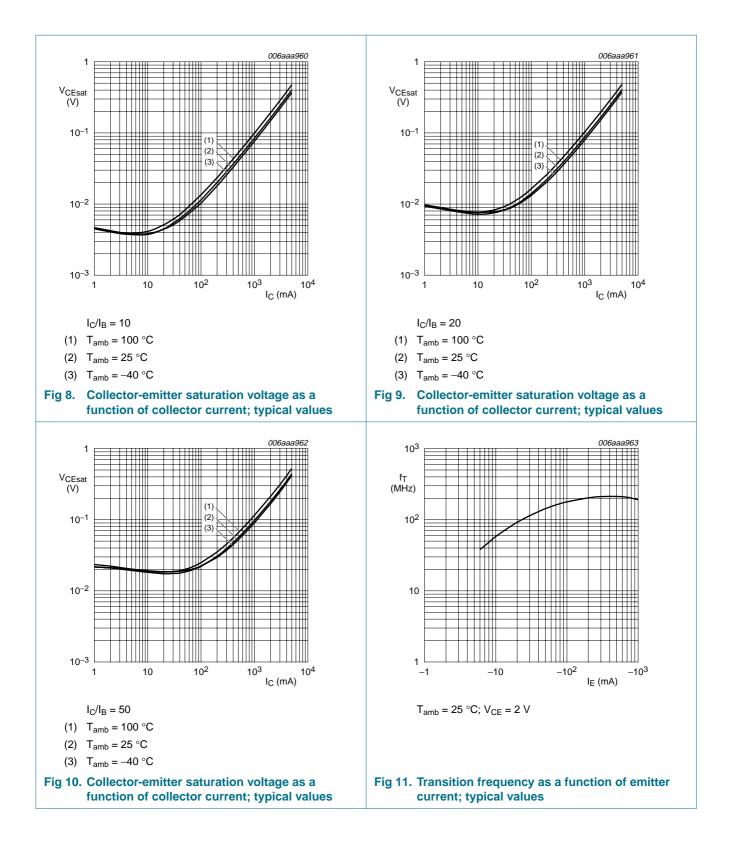
2PD2150

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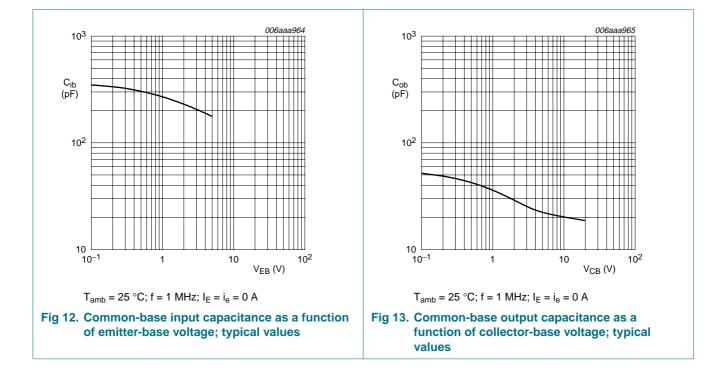
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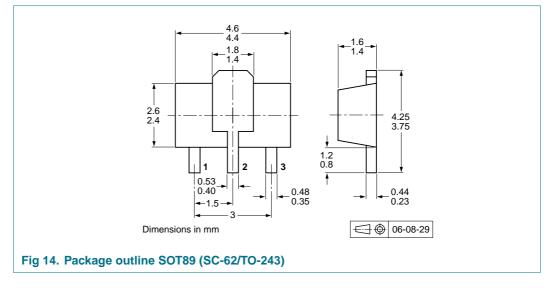
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8. Package outline

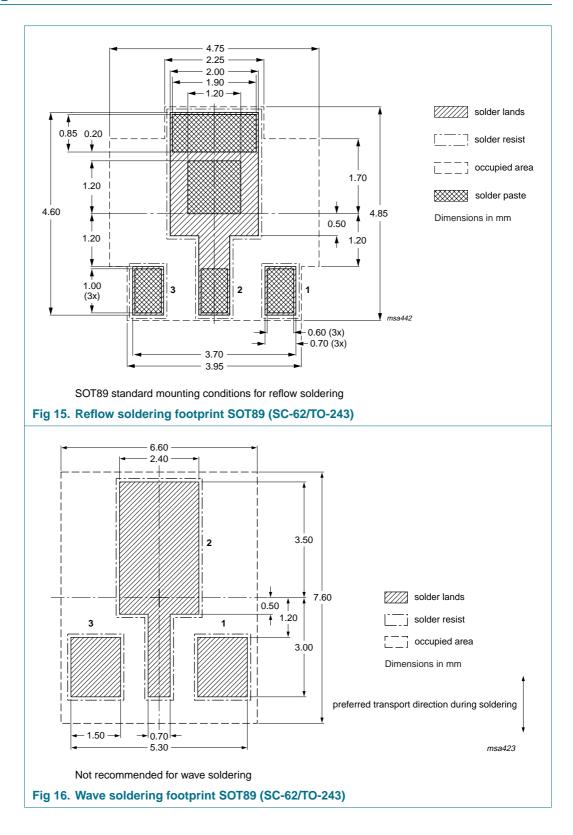


9. Packing information

Please refer to packing information on <u>www.nexperia.com</u>.

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10. Soldering



11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
2PD2150_2	20070102	Product data sheet	-	2PD2150_1		
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply w	vith the new identity		
	 Legal texts 	have been adapted to the n	ew company name whe	ere appropriate.		
	Table 1 "Qu	ick reference data": I _C colle	ctor current added			
	Table 1 "Qu	ick reference data": I _{CM} pea	ak collector current max	imum value adapted		
	 Table 1 "Quick reference data": V_{CEsat} collector-emitter saturation voltage added 					
	 Table 5 "Limiting values": V_{CEO} collector-emitter voltage maximum value adapted 					
	 <u>Table 5 "Limiting values"</u>: I_C collector current maximum value adapted 					
	 <u>Table 5 "Limiting values"</u>: I_{CM} peak collector current maximum value adapted 					
	 <u>Table 5 "Limiting values"</u>: P_{tot} total power dissipation for ceramic PCB condition added 					
	Figure 1 "Power derating curves": adapted					
	Table 6 "Thermal characteristics": adapted					
	 <u>Table 6 "Thermal characteristics"</u>: R_{th(j-a)} thermal resistance from junction to ambient for ceramic PCB condition added 					
	 Figure 2: t_p pulse time redefined to pulse duration 					
	• Figure 3: added					
	 Table 7 "Characteristics": V_{CEsat} collector-emitter saturation voltage typical value added 					
	 Table 7 "Ch 	aracteristics": f _T transition fr	equency conditions slig	htly changed		
	 Table 7 "Characteristics": C_{ib} common-base input capacitance added 					
	 Table 7 "Characteristics": Cob common-base output capacitance added 					
	 Figure 4, 6, 10, 11, 12, 13 and 16: added 					
	 Figure 5, 7, 8 and 9: adapted 					
		Legal information": updated	b			
2PD2150 1	20050422	Product data sheet	-	-		

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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